

REMARKS

This paper is in response to the official action of July 8, 2005. Reconsideration is requested.

By the foregoing, claim 1 has been amended to recite forming a tungsten silicide film by reacting SiH_4 or SiH_2Cl_2 with WF_6 at a stoichiometric ratio of the silicon compound to the tungsten compound of 2.0 to 2.8. Support is found at page 6, lines 8-12 of the specification. The remaining claims have been amended for consistency with claim 1 and for clarity, and claim 4 has been canceled.

Claims 1-3 and 5-8 are at issue.

The anticipation rejection of claims 1-5 and 8 based on Chang et al. U.S. 6,380,029, and the obviousness rejection of claims 6 and 7 based on the combination of Chang with Xu et al. U.S. 6,544,896 are respectfully but strongly traversed. Reconsideration is requested.

As disclosed in the specification at page 6, the tungsten silicide film made according to the invention has good step coverage and a surface resistance and the surface resistance of the tungsten silicide film is minimized.

It is submitted that the applied references do not teach or suggest the stoichiometric ratio of reactants recited in the present claims, and thus do not teach or suggest the presently claimed method, which results in the favorable attributes of the invention.

As a result, it is believed that the claims at issue are clearly patentably over the applied references, and an indication to that effect is solicited.

Should the examiner wish to discuss the foregoing or any matter of form in an effort to advance this application toward allowance, he is urged to telephone the undersigned at the indicated number.

Respectfully submitted,

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